IN THE CLAIMS

Please amend the claims as follows:

Claims 1-27 (Cancelled)

Claim 28 (New) A process for manufacturing a substrate, at least one part of the surface of the substrate has been rendered hydrophobic, wherein said hydrophobic surface structure comprises an essentially mineral silicon-containing sublayer formed at least partly on the surface of the substrate, and an outer layer of hydrophobic agent grafted onto said sublayer, wherein said sublayer had a surface that was in an activated state before being brought into contact with said hydrophobic agent, wherein said process comprises:

treating a surface of the silicon-containing mineral layer to activate the surface of the silicon-containing mineral layer in at least one pass, depositing the coating layer of hydrophobic agent, in at least one pass, on the surface, in the activated state, of the silicon-containing mineral layer formed at least partly on the surface of the substrate and

wherein said treating is carried out under conditions that allow a silicon-containing layer to be etched, with a plasma of at least one fluorine-containing gas chosen from SF_6, CF_4, C_2F_6 and other fluorinated gases, optionally combined with oxygen in an amount up to 50% by volume of the etching plasma.

29. (New) The process according to Claim 28, wherein the hydrophobic agent is deposited within a time of from 1 second to 15 minutes, after the activation of the surface of the silicon-containing mineral layer.

30. (New) The process according to Claim 28, wherein the activation is monitored.

31. (New) The process according to Claim 28, wherein the silicon-containing layer is deposited, cold, on the substrate by vacuum cathode sputtering.

32. (New) The process according to Claim 31, wherein the silicon-containing layer is deposited, cold, on the substrate by magnetron sputtering, ion beam sputtering, or by low-

pressure plasma-enhanced chemical vapour deposition (PECVD), or atmospheric- pressure PECVD.

33. (New) The process according to Claim 32, further comprising depositing a layer of SiO_2, as silicon-containing layer, by PECVD, with a mixture of an organic or nonorganic, silicon-containing precursor and an oxidizer, wherein the subsequent activation being carried out in the same chamber or in a separate chamber.

34. (New) The process according to Claim 33, wherein the silicon-containing precursor is SiH_4, hexamethyldisiloxane, tetraethoxysilane and tetramethyldisiloxane.

35. (New) The process according to one of the preceding claims, wherein the outer layer of hydrophobic agent is based on a hydrophobic agent is a fluorosilane and wherein the fluorosilane layer is deposited by wiping-on, evaporation or spraying of a solution containing the fluorosilane, or by dipping, spin-coating, or flow-coating with a solution containing the fluorosilane.

36. (New) The process according to Claim 28, wherein the substrate is formed by a plate, whether plane or with curved faces, of monolithic or laminated glass, of glass-ceramic or of a hard thermoplastic.

37. (New) The process according to Claim 28, wherein said sublayer is formed by a compound chosen from SiO_x, where $x \leq 2$, SiOC, SiON, SiOCN and Si_3N_4, it being possible for hydrogen to be combined in all proportions with SiO_x, where $x \leq 2$, SiOC, SiON and SiOCN

38. (New) The process according to Claim 28, wherein the silicon-containing sublayer comprises aluminum or carbon, Ti, Zr, Zn and S.

39. (New) The process according to Claim 38, wherein the silicon-containing sublayer comprises aluminum in an amount up to 8% by weight.

40. (New) The process according to Claim 28, wherein the activated surface of the silicon-containing sublayer has a thickness of 20 nm to 250 nm.

41. (New) The process according to Claim 28, wherein the activated surface of the silicon-containing sublayer has a thickness of 30 nm to 100 nm.

42. (New) The process according to Claim 28, wherein the activated surface of the silicon-containing sublayer has a thickness of 30 nm to 75 nm.

43. (New) The process according to Claim 28, wherein the activated surface of the silicon-containing sublayer has an RMS roughness of 0.1 nm to 40 nm.

44. (New) The process according to Claim 28, wherein the activated surface of the silicon-containing sublayer has an actual developed area at least 40% greater than the initial plane area.

45. (New) The process according to Claim 28, wherein the outer layer of hydrophobic agent is based on a hydrophobic agent is:

(a) an alkylsilane of formula (I):

$$CH_3(CH_2)_nSiR_mX_{3-m} \qquad (I)$$

in which:

n ranges from 0 to 30, more particularly from 0 to 18;

m = 0, 1, 2 or 3;

R represents an optionally functionalized organic chain; and

X represents a hydrolyzable residue that is an OR^0 residue, where R^0 represents hydrogen; or a linear, branched or cyclic alkyl residue, an aryl residue; or a halo residue;

(b) a compound with grafted silicone chains;

(c) a fluorosilane that has a formula (II):

$$R^1\text{-}A\text{-}SiR_p^2X_{3-p} \qquad (II)$$

in which:

R^1 represents an C_1-C_9 monofluoroalkyl, oligofluoroalkyl or perfluoroalkyl residue; or a monoaryl, oligoaryl or perfluoroaryl residue;

A represents a hydrocarbon chain, optionally interrupted by a heteroatom selected from O or S;

R^2 represents a linear, branched or cyclic alkyl residue, or an aryl residue; X represents a hydrolyzable residue that is an OR^3 residue, where R^3 represents hydrogen or a linear, branched or cyclic, alkyl residue; an aryl residue; or a halo residue; and

p = 0, 1 or 2.

46. (New) The process according to Claim 28, wherein the layer of hydrophobic agent has a weight per unit area of grafted fluorine of 0.1 $\mu g/cm^2$ and 3.5 $\mu g/cm^2$.